



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Data Sheet

Description

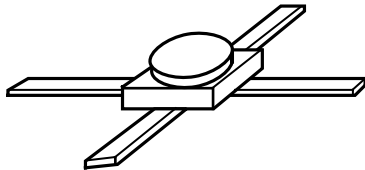
The MSA-0270 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic, high reliability package. This MMIC is designed for use as a general purpose 50 Ω gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using Avago's 10 GHz f_T , 25 GHz f_{MAX} , silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

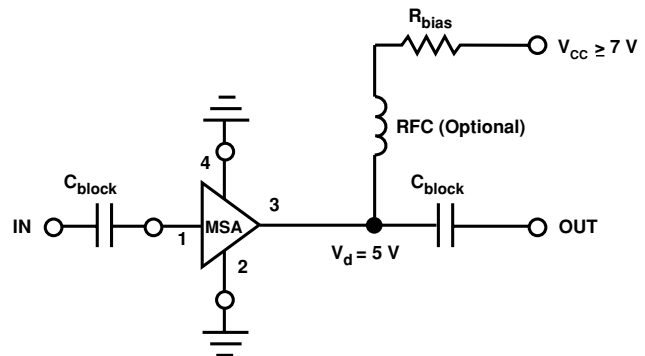
Features

- Cascadable 50 Ω Gain Block
- 3 dB Bandwidth: DC to 2.8 GHz
- 12.0 dB Typical Gain at 1.0 GHz
- Unconditionally Stable ($k > 1$)
- Hermetic Gold-ceramic Microstrip Package

70 mil Package



Typical Biasing Configuration



MSA-0270 Absolute Maximum Ratings

Parameter	Absolute Maximum ^[1]
Device Current	60 mA
Power Dissipation ^[2,3]	325 mW
RF Input Power	+13 dBm
Junction Temperature	200°C
Storage Temperature	−65 to 200°C

Thermal Resistance^[2,4]:

$$\theta_{jc} = 120^{\circ}\text{C/W}$$

Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2. $T_{\text{CASE}} = 25^{\circ}\text{C}$.
3. Derate at 8.3 mW/°C for $T_C > 161^{\circ}\text{C}$.
4. The small spot size of this technique results in a higher, though more accurate determination of θ_{jc} than do alternate methods.

Electrical Specifications^[1], $T_A = 25^{\circ}\text{C}$

Symbol	Parameters and Test Conditions: $I_d = 25 \text{ mA}$, $Z_0 = 50 \Omega$	Units	Min.	Typ.	Max.
G_p	Power Gain ($ S_{21} ^2$) $f = 0.1 \text{ GHz}$	dB	11.5	12.5	13.5
ΔG_p	Gain Flatness $f = 0.1 \text{ to } 1.8 \text{ GHz}$	dB		± 0.6	± 1.0
$f_{3 \text{ dB}}$	3 dB Bandwidth	GHz		2.8	
VSWR	Input VSWR $f = 0.1 \text{ to } 3.0 \text{ GHz}$			1.4:1	
	Output VSWR $f = 0.1 \text{ to } 3.0 \text{ GHz}$			1.4:1	
NF	50 Ω Noise Figure $f = 1.0 \text{ GHz}$	dB		6.5	
$P_{1 \text{ dB}}$	Output Power at 1 dB Gain Compression $f = 1.0 \text{ GHz}$	dBm		4.5	
IP_3	Third Order Intercept Point $f = 1.0 \text{ GHz}$	dBm		17.0	
t_D	Group Delay $f = 1.0 \text{ GHz}$	psec		125	
V_d	Device Voltage	V	4.5	5.0	5.5
dV/dT	Device Voltage Temperature Coefficient	mV/°C		−8.0	

Note:

1. The recommended operating current range for this device is 18 to 40 mA. Typical performance as a function of current is on the following page.

MSA-0270 Typical Scattering Parameters ($Z_0 = 50 \Omega$, $T_A = 25^\circ\text{C}$, $I_d = 25 \text{ mA}$)

Freq. GHz	S_{11}			S_{21}			S_{12}		S_{22}	
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.11	179	12.6	4.26	176	-18.4	.120	1	.12	-8
0.2	.11	174	12.6	4.24	171	-18.6	.117	3	.12	-15
0.4	.10	169	12.5	4.21	162	-18.4	.120	4	.13	-30
0.6	.09	165	12.4	4.17	154	-18.2	.123	5	.14	-44
0.8	.08	161	12.3	4.11	146	-18.2	.123	7	.14	-55
1.0	.06	161	12.2	4.05	137	-18.0	.126	9	.15	-64
1.5	.02	-150	11.7	3.85	116	-17.2	.138	11	.16	-84
2.0	.06	-110	11.1	3.57	96	-16.3	.153	11	.16	-102
2.5	.11	-112	10.3	3.27	82	-15.7	.165	14	.14	-106
3.0	.17	-134	9.3	2.92	65	-15.2	.174	12	.13	-114
3.5	.22	-147	8.2	2.56	48	-14.7	.185	6	.15	-111
4.0	.26	156	7.0	2.23	33	-14.3	.192	3	.19	-107
5.0	.28	179	4.7	1.72	8	-14.0	.199	-6	.27	-107
6.0	.30	143	3.0	1.41	-13	-13.8	.204	-14	.29	-119

Typical Performance, $T_A = 25^\circ\text{C}$

(unless otherwise noted)

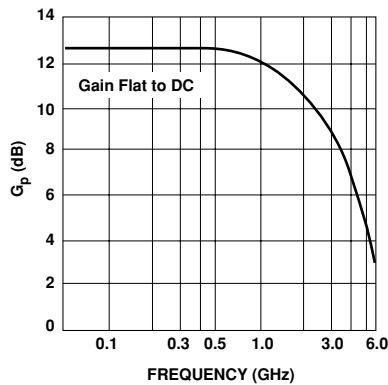


Figure 1. Typical Power Gain vs. Frequency, $T_A = 25^\circ\text{C}$, $I_d = 25 \text{ mA}$.

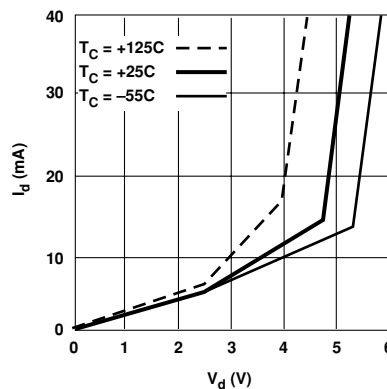


Figure 2. Device Current vs. Voltage.

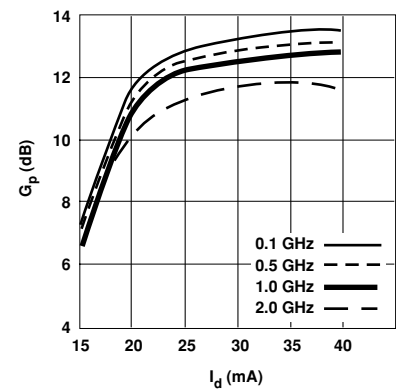


Figure 3. Power Gain vs. Current.

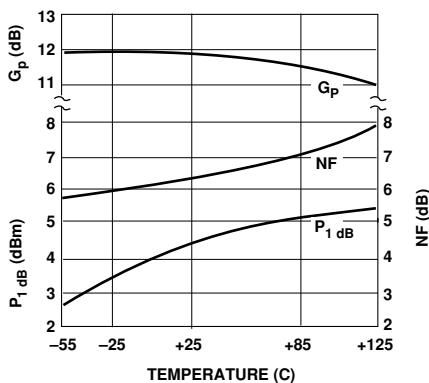


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Mounting Surface Temperature, $f = 1.0 \text{ GHz}$, $I_d = 25 \text{ mA}$.

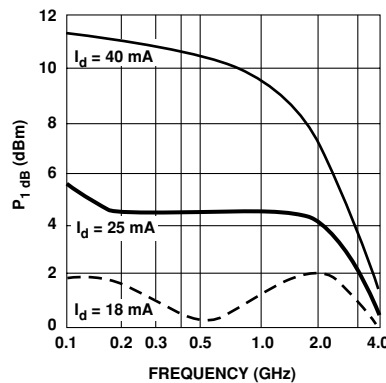


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

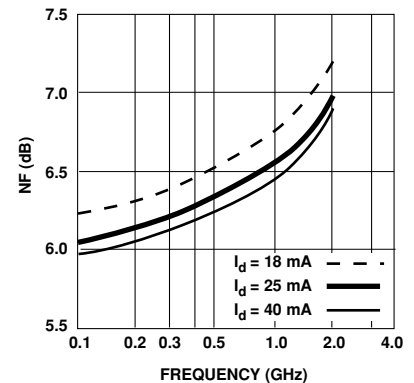
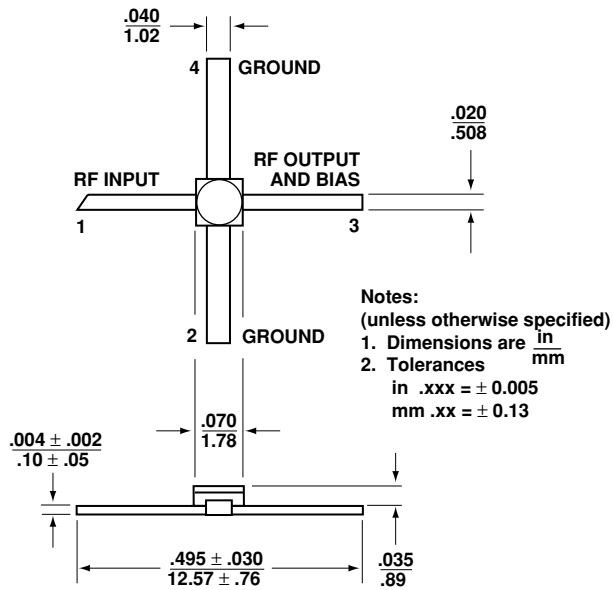


Figure 6. Noise Figure vs. Frequency.

Ordering Information

Part Number	No. of Devices	Comments
MSA-0270	100	Bulk

70 mil Package Dimensions



For product information and a complete list of distributors, please go to our web site: www.avagotech.com

Avago, Avago Technologies, and the A logo are trademarks of Avago Technologies, Limited in the United States and other countries. Data subject to change. Copyright © 2008 Avago Technologies, Limited. All rights reserved. Obsoletes 5989-2766EN AV02-1223EN May 5, 2008

AVAGO
TECHNOLOGIES